METHOD FOR PRODUCING BONDED WAFER

ABSTRACT OF THE DISCLOSURE

A bonded wafer is produced by a method comprising a step of implanting ions of a light element such as hydrogen, helium or the like into a wafer for active layer at a predetermined depth position to form an ion implanted layer, a step of bonding the wafer for active layer to a wafer for support substrate through an insulating film, a step of exfoliating the wafer at the ion implanted layer, a first heat treatment step of conducting a sacrificial oxidation for reducing damage on a surface of an active layer exposed through the exfoliation and a second heat treatment step of raising a bonding strength, in which the second heat treatment step is continuously conducted after the first heat treatment step without removing an oxide film formed on the surface of the active layer.

Fig. 1